

# SMD Schottky Barrier Diode

**COMCHIP**  
SMD Diodes Specialist

## CDBUR00340(RoHs Device)

**I<sub>o</sub> = 30 mA**

**V<sub>R</sub> = 40 Volts**



### Features

Designed for mounting on small surface.

Extremely thin package.

Low stored charge.

Majority carrier conduction.

### Mechanical data

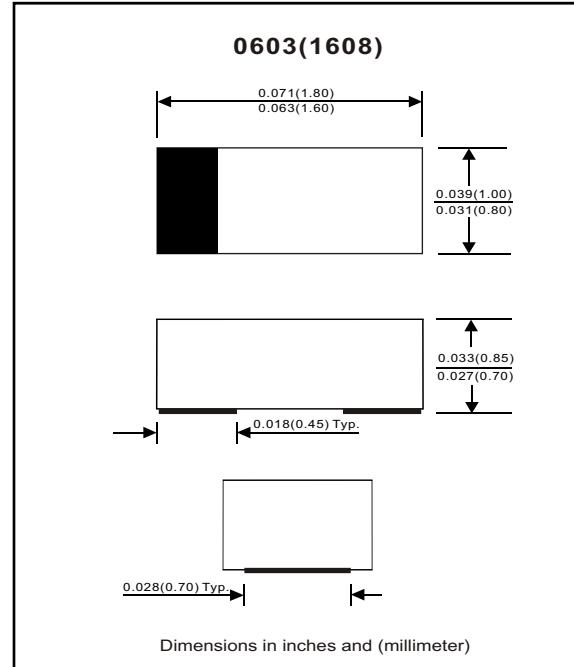
Case: 0603(1608) standard package,  
molded plastic.

Terminals: Gold plated, solderable per  
MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.003 gram(approx.).



### Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V <sub>RRM</sub>			45	V
Reverse voltage		V <sub>R</sub>			40	V
Average forward current		I <sub>o</sub>			30	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I <sub>FSM</sub>		500		mA
Power Dissipation		P <sub>D</sub>			150	mW
Sunction temperature		T <sub>TSG</sub>	-40		+125	°C
Junction temperature		T <sub>j</sub>			+125	°C

### Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 1 mA DC	V <sub>F</sub>			0.37	V
Reverse current	V <sub>R</sub> = 30V V <sub>R</sub> = 40V	I <sub>R</sub>			0.50 1.00	uA
Capacitance between terminals	F = 1 MHZ and 1 VDC reverse voltage	C <sub>T</sub>		1.5		pF

## RATING AND CHARACTERISTIC CURVES (CDBUR00340)

Fig. 1 - Forward characteristics

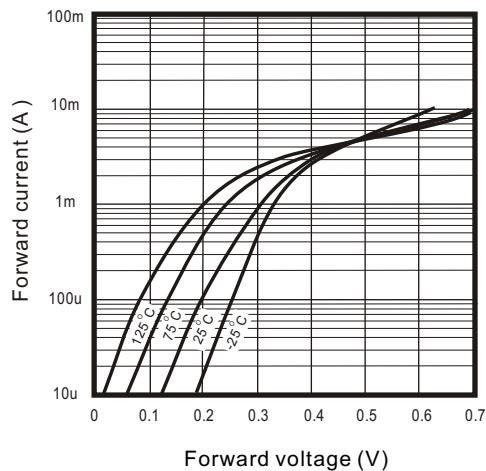


Fig. 2 - Reverse characteristics

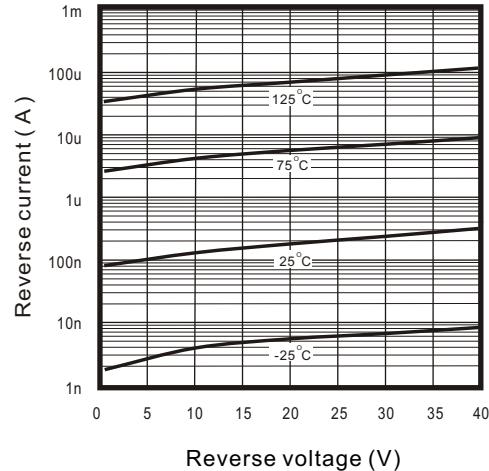


Fig.3 - Capacitance between terminals characteristics

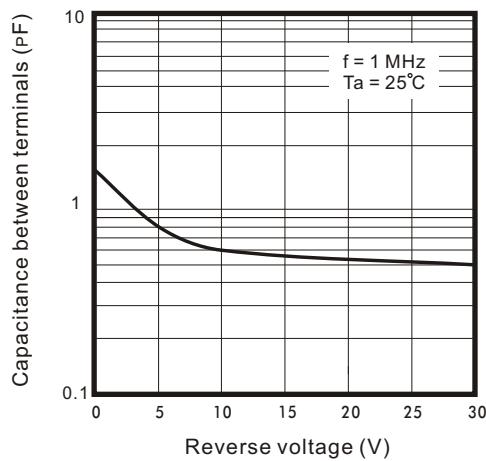


Fig.4 - Current derating curve

